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WAFER PLATING DEVICE

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor wafer plating device capable of uniformizing the plating film thickness in each part of the surface of a semiconductor wafer and capable of uniformly and securely applying the insides of a plurality of fine grooves and fine pores formed on the surface of the semiconductor wafer with plating.

SOLUTION: The inside of a cylindrical anode case 30 is stored with an anode 40 and an ascending vortical flow generating mechanism generating an ascending vortical flow in a plating soln. in the anode case 30. In a state in which the anode case 30 is set directly above a plating forming region on a semiconductor wafer 100, the plating forming region part is subjected to electrolytic plating. The ascending vortical flow generating mechanism 50 is

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composed in such a manner that a rotary shaft 41 pivoted with the anode 40 is provided with a blade 51.

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